BLM10D1822-61ABG

LDMOS 2-stage integrated Doherty MMIC

AMPLEON

Rev. 1 — 19 October 2020

Product data sheet

1. Product profile

1.1 General description

The BLM10D1822-61ABG is a 2-stage fully integrated Doherty MMIC solution using Ampleon's state of the art GEN10 LDMOS technology. The carrier and peaking device, input splitter and output combiner are integrated in a single package. This multiband device is perfectly suited as general purpose driver in the frequency range from 1800 MHz to 2200 MHz. Available in gull wing.

Table 1. Performance

Typical RF performance at $T_{case} = 25$ °C; $I_{Dq} = 100$ mA (carrier); $V_{GSq(peaking)} = V_{GSq(carrier)} - 0.36$ V. Test signal: 1-carrier LTE; carrier spacing = 20 MHz; PAR = 7.6 dB at 0.01 % probability on CCDF.

Test signal	f	V _{DS}	P _{L(M)}	G _p	η _D	ACPR _{20M}
	(MHz)	(V)	(dBm)	(dB)	(%)	(dBc)
1-carrier LTE 20 MHz	1990	28	40	27.5	42.5	-32

1.2 Features and benefits

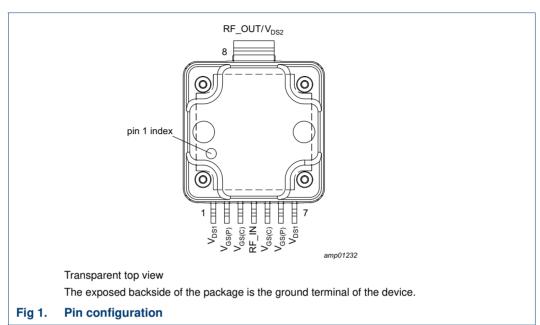
- Integrated input splitter
- Integrated output combiner
- High efficiency
- Designed for broadband operation (frequency 1800 MHz to 2200 MHz)
- Integrated temperature compensated bias
- Independent control of carrier and peaking bias
- Integrated ESD protection
- Excellent thermal stability
- Source impedance 50 Ω ; high power gain
- For RoHS compliance see the product details on the Ampleon website

1.3 Applications

■ RF power MMIC for multi-carrier and multi-standard GSM, W-CDMA and LTE base stations in the 1800 MHz to 2200 MHz frequency range

2. Pinning information

2.1 Pinning



2.2 Pin description

Table 2. Pin description

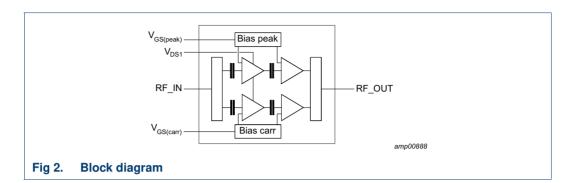
Symbol	Pin	Description
V _{DS1}	1	drain-source voltage of driver stages
V _{GS(P)}	2	gate-source voltage of peaking P
V _{GS(C)}	3	gate-source voltage of carrier C
RF_IN	4	RF input
V _{GS(C)}	5	gate-source voltage of carrier C
V _{GS(P)}	6	gate-source voltage of peaking P
V _{DS1}	7	drain-source voltage of driver stages
RF_OUT/V _{DS2}	8	RF output / drain-source voltage of final stages
GND	flange	RF ground

3. Ordering information

Table 3. Ordering information

Type number	Packag	Package					
	Name	Description	Version				
BLM10D1822-61ABG		plastic, heatsink small outline package; 8 leads	OMP-400-8G-1				

4. Block diagram



5. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	65	V
V_{GS}	gate-source voltage		-6	+9	V
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature	[1]	-	200	°C
T _{case}	case temperature		-	150	°C
Pi	input power	[2]	-	13	dBm

^[1] Continuous use at maximum temperature will affect the reliability. For details refer to the online MTF calculator.

6. Thermal characteristics

Table 5. Thermal characteristics

Measured for total device.

Symbol	Parameter	Conditions	Value	Unit
R _{th(j-c)}	thermal resistance from junction to	$T_{case} = 90 ^{\circ}C; P_{L} = 10 W$ [1]	1.9	K/W
	case	$T_{case} = 90 ^{\circ}C; P_{L} = 2.5 W$ [1]	2.7	K/W

^[1] When operated with a 1-carrier W-CDMA with PAR = 9.9 dB.

^[2] $T_{case} = 25$ °C; $V_{DS} = 28$ V; $I_{Dq} = 108$ mA (carrier and peaking); $V_{GSq(peaking)} = V_{GSq(carrier)} - 0.36$ V. Test signal: 1-carrier LTE 20 MHz, PAR = 7.6 dB at 0.01 % probability CCDF.

7. Characteristics

Table 6. DC characteristics

 $T_{case} = 25 \, ^{\circ}C$.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	f > 2000 MHz; up to 2 : 1 output impedance mismatch	[1]	-	28	32	V
		$f \le 2000$ MHz; up to $5:1$ output impedance mismatch	[1]	-	28	32	٧
		all frequencies; up to 5 : 1 output impedance mismatch	[1]	-	28	30	V
Carrier							
V_{GSq}	gate-source quiescent voltage	$V_{DS} = 28 \text{ V}; I_D = 100 \text{ mA}$		1.6	2.1	2.7	V
I _{GSS}	gate leakage current	V _{GS} = 9 V; V _{DS} = 0 V		-	-	140	nA
Peaking							
I _{GSS}	gate leakage current	V _{GS} = 9 V; V _{DS} = 0 V		-	-	140	nA
Final sta	ges						
I _{DSS}	drain leakage current	V _{GS} = 0 V; V _{DS} = 28 V		-	-	1.4	μΑ
Driver st	ages						
I _{DSS}	drain leakage current	$V_{GS} = 0 \text{ V}; V_{DS} = 28 \text{ V}$		-	-	1.4	μА

^[1] $I_{Dq} = 108$ mA (carrier and peaking); $V_{GSq(peaking)} = V_{GSq(carrier)} - 0.36$ V. Test signal: 1-carrier LTE 20 MHz, PAR = 7.6 dB at 0.01 % probability CCDF.

Table 7. RF Characteristics

Typical RF performance at T_{case} = 25 °C; V_{DS} = 28 V; I_{Dq} = 100 mA (carrier); $V_{GSq(peaking)}$ = $V_{GSq(carrier)}$ – 0.36 V; $P_{L(AV)}$ = 10 W; unless otherwise specified measured in an Ampleon production circuit.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Tested s	ignal: pulsed CW [1]					
G _p	power gain	f = 2000 MHz	26.5	28.5	30.5	dB
η_{D}	drain efficiency	$P_L = 10 \text{ W } (40 \text{ dBm})$	40	45	-	%
		$P_L = P_{L(3dB)}$	44	51	-	%
RLin	input return loss		-	-15	-10	dB
P _{L(3dB)}	output power at 3 dB gain compression		47.1	47.8	-	dBm

^[1] Pulsed CW power sweep measurement (δ = 10 %, t_p = 100 μ s).

8. Application information

Table 8. Typical performance

 $T_{case} = 25$ °C; $V_{DS} = 28$ V; $I_{Dq} = 100$ mA (driver and final stages). Test signal: 1-carrier LTE 20 MHz, PAR 7.6 dB at 0.01 % probability CCDF; unless otherwise specified, typical performance in an Ampleon 1805 MHz to 2200 MHz frequency band asymmetrical integrated Doherty application circuit.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$P_{L(M)}$	peak output power	f = 1990 MHz	[1]	-	48.3	-	dBm
φ _{s21} /φ _{s21(norm)}	normalized phase response	f = 1990 MHz; at 3 dB compression point;	[2]	-	-24.5	-	0
η_{D}	drain efficiency	13 dB OBO (P _{L(AV)} = 35 dBm); f = 1990 MHz		-	29.6	-	%
		13 dB OBO (P _{L(AV)} = 35 dBm); f = 1990 MHz	[3]	-	28.7	-	%
Gp	power gain	P _{L(AV)} = 35 dBm; f = 1990 MHz		-	27.8	-	dB
B _{video}	video bandwidth	P _{L(AV)} = 38 dBm, set to obtain IMD3 = -25 dBc; 2-tone CW; f = 1990 MHz		-	618	-	MHz
G _{flat}	gain flatness	$P_{L(AV)} = 35 \text{ dBm}$; f = 1805 MHz to 2200 MHz		-	0.6	-	dB
ACPR _{20M}	adjacent channel power ratio (20 MHz)	P _{L(AV)} = 35 dBm; f = 1990 MHz		-	-35.6	-	dB
ΔG/ΔΤ	gain variation with temperature	f = 1990 MHz	[4]	-	0.06	-	dB/°C
K	Rollett stability factor	$T_{case} = -40$ °C; f = 0.2 GHz to 6.1 GHz	[4]	-	>1	-	

^[1] Test signal: 1-carrier W-CDMA; test model 1; 64 DPCH; PAR = 9.9 dB at 0.01 % probability CCDF.

^{[2] 25} ms CW power sweep measurement.

^[3] Test signal: 2-carrier LTE 20 MHz spaced by 345 MHz, PAR = 8 dB at 0.01 % probability CCDF linearized.

^[4] S-parameters measured with broadband demo board.

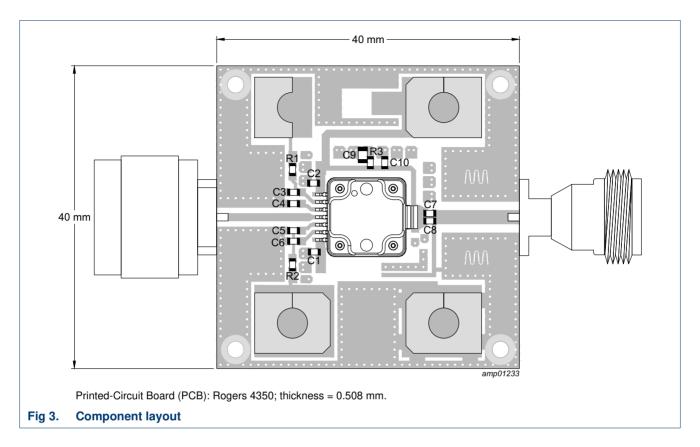
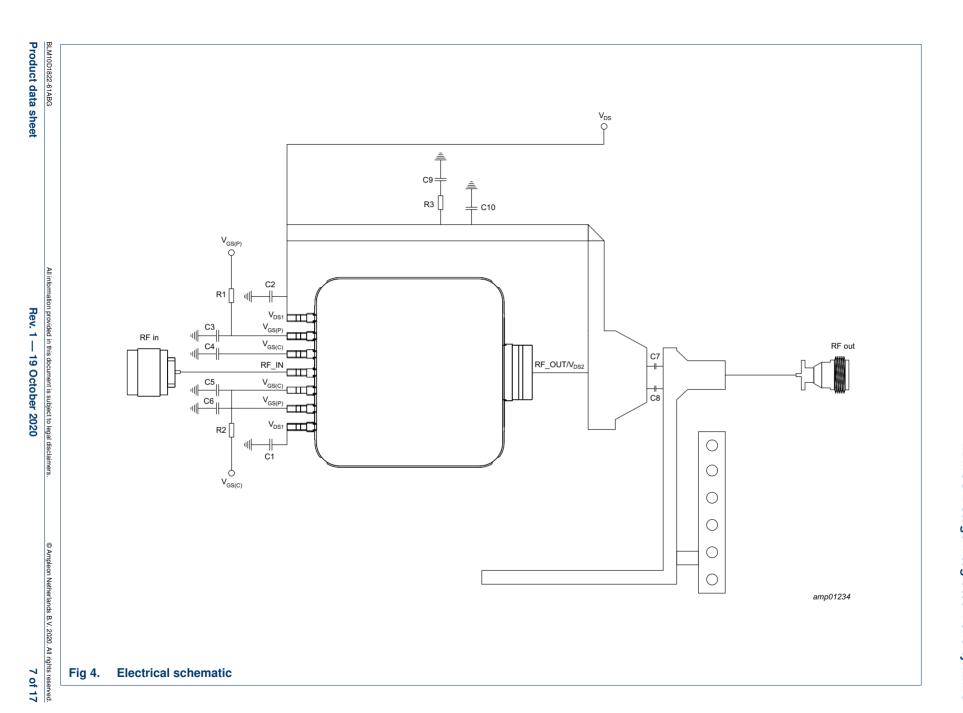


Table 9. Demo test circuit list of components

See Figure 3 for component layout.

Component	Description	Value	Remarks
C1, C2	multilayer ceramic chip capacitor	10 μF, 35 V	TDK: C2012X5R1V106K SMD 0805
C3, C4, C5, C6	multilayer ceramic chip capacitor	4.7 μF, 6.3 V	AVX: 06036D106MAT2A SMD 0603
C7	multilayer ceramic chip capacitor	1 pF	Murata: GQM1875C2E1R0WB12D SMD 0603
C8	multilayer ceramic chip capacitor	0.9 pF	Murata: GQM1875C2ER90BB12D SMD 0603
C9	multilayer ceramic chip capacitor	10 μF, 50 V	TDK: C2012X5R1V106K SMD 0805
C10	multilayer ceramic chip capacitor	9.1 pF	Murata: GQM1875C2E9R1CB12D SMD 0603
R1, R2	resistor	0 Ω	Multicomp: SMD 0603
R3	resistor	3 Ω	Multicomp: SMD 0603



8.1 Ruggedness in a Doherty operation

The BLM10D1822-61ABG is capable of withstanding a load mismatch corresponding to VSWR = 5 : 1 through all phases under the following conditions: V_{DS} = 30 V; I_{Dq} = 108 mA (carrier and peaking); $V_{GSq(peaking)}$ = $V_{GSq(carrier)}$ – 0.36 V; P_i corresponding to 41 dBm under Z_S = 50 Ω load; f = 2170 MHz (test signal: 1-carrier LTE 20 MHz, PAR = 7.6 dB at 0.01 % probability CCDF, is used during the stress); T_{case} = 25 °C. In such VSWR conditions, it is recommended not to exceed 30 V for the operating supply voltage.

The BLM10D1822-61ABG is capable of withstanding a 400 MHz white noise signal at 2 GHz (P_L = 42 dBm), 1.805 GHz (P_L = 38 dBm), 2.17 GHz (P_L = 38 dBm) or a 50 MHz white noise signal at 2.170 GHz (P_L = 42 dBm).

Conditions: V_{DS} = 28 V, I_{Dq} = 108 mA (carrier and peaking), T_{case} = 25 °C.

8.2 Impedance information

Table 10. Typical impedance for optimum Doherty operation

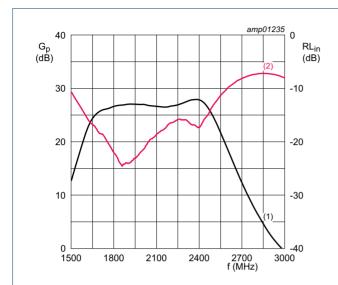
Measured load-pull data per section; test signal: pulsed CW; T_{case} = 25 °C; V_{DS} = 28 V; I_{Dq} = 100 mA (carrier); $V_{GSq(peaking)}$ = $V_{GSq(carrier)}$ – 0.36 V; t_p = 100 μ s; δ = 10 %. Typical values per section unless otherwise specified.

	tuned for optimum	tuned for optimum Doherty operation							
f	Z _L	G _{p(max)}	PL	η _{add} [1]	η _{add} [2]				
(MHz)	(Ω)	(dB)	(dBm)	(%)	(%)				
1800	22.816 – j6.170	28.597	48.273	48.836	46.255				
1900	22.187 – j2.743	29.207	48.088	51.479	47.814				
2000	20.708 - j7.364	28.915	48.032	52.069	46.803				
2100	22.706 – j4.197	28.620	48.100	56.063	46.777				
2200	22.076 – j1.029	28.209	47.700	57.646	47.034				

^[1] At 3 dB gain compression point.

^[2] At $P_L = 40 \text{ dBm}$.

8.3 Graphs



 $T_{case} = 25 \, ^{\circ}C; \, V_{DS} = 28 \, V;$

 $I_{Dq1} + I_{Dq2} = 100 \text{ mA}$ (carrier and peaking stages);

 $V_{GS} = 2.19 \text{ V (carrier stage)};$

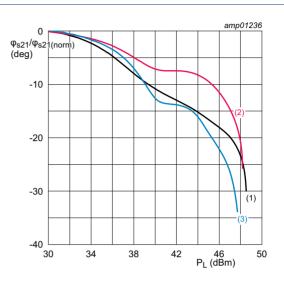
V_{GS} = 1.87 V (peaking stage).

Test signal: CW.

(1) magnitude of Gp

(2) magnitude of RLin

Fig 5. Wideband power gain and input return loss as function of frequency; typical values



 $T_{case} = 25 \, ^{\circ}C; \, V_{DS} = 28 \, V;$

 $I_{Dq1} + I_{Dq2} = 100 \text{ mA (carrier and peaking stages)};$

 $V_{GS} = 2.19 \text{ V (carrier stage)};$

V_{GS} = 1.87 V (peaking stage).

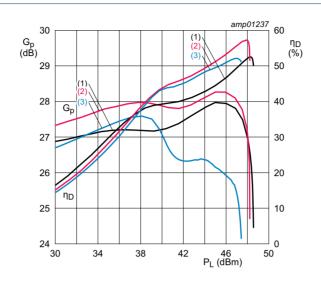
Test signal: 25 ms CW power sweep.

(1) f = 1805 MHz

(2) f = 1990 MHz

(3) f = 2200 MHz

Fig 6. Normalized phase response as a function of output power; typical values

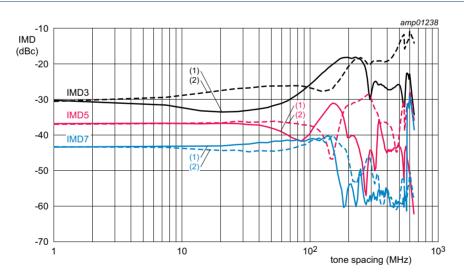


 T_{case} = 25 °C; V_{DS} = 28 V; I_{Dq1} + I_{Dq2} = 100 mA (carrier and peaking stages); V_{GS} = 2.19 V (carrier stage); V_{GS} = 1.87 V (peaking stage).

Test signal: pulsed CW power sweep (δ = 10 %; t_p = 100 μ s).

- (1) f = 1805 MHz
- (2) f = 1990 MHz
- (3) f = 2200 MHz

Fig 7. Power gain and drain efficiency as function of output power; typical values

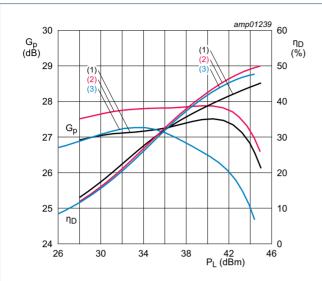


 T_{case} = 25 °C; V_{DS} = 28 V; I_{Dq1} + I_{Dq2} = 100 mA (carrier and peaking stages); V_{GS} = 2.19 V (carrier stage); V_{GS} = 1.87 V (peaking stage).

Test signal: 2-tone CW; $f_c = 1990 \text{ MHz}$.

- (1) IMD low
- (2) IMD high

Intermodulation distortion as a function of tone spacing; typical values Fig 8.



 T_{case} = 25 °C; V_{DS} = 28 V;

 $I_{Dq1} + I_{Dq2} = 100$ mA (carrier and peaking stages);

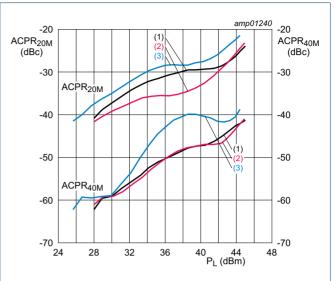
 $V_{GS} = 2.19 \text{ V (carrier stage)};$

V_{GS} = 1.87 V (peaking stage).

Test signal: 1-carrier LTE; PAR = 7.6 dB at 0.01 % probability CCDF.

- (1) f = 1805 MHz
- (2) f = 1990 MHz
- (3) f = 2200 MHz

Fig 9. Power gain and drain efficiency as function of output power; typical values



 $T_{case} = 25 \, ^{\circ}C; \, V_{DS} = 28 \, V;$

 $I_{Dq1} + I_{Dq2} = 100$ mA (carrier and peaking stages);

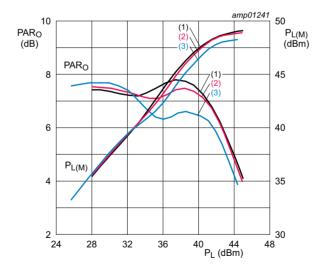
V_{GS} = 2.19 V (carrier stage);

V_{GS} = 1.87 V (peaking stage).

Test signal: 1-carrier LTE; PAR = 7.6 dB at 0.01 % probability CCDF.

- (1) f = 1805 MHz
- (2) f = 1990 MHz
- (3) f = 2200 MHz

Fig 10. Adjacent channel power ratio as a function of output power; typical values



 T_{case} = 25 °C; V_{DS} = 28 V; I_{Dq1} + I_{Dq2} = 100 mA (carrier and peaking stages);

V_{GS} = 2.19 V (carrier stage); V_{GS} = 1.87 V (peaking stage).

Test signal: 1-carrier LTE; PAR = 7.6 dB at 0.01 % probability CCDF.

- (1) f = 1805 MHz
- (2) f = 1990 MHz
- (3) f = 2200 MHz

Fig 11. Output peak-to-average ratio and peak output power as function of output power; typical values

9. Package outline

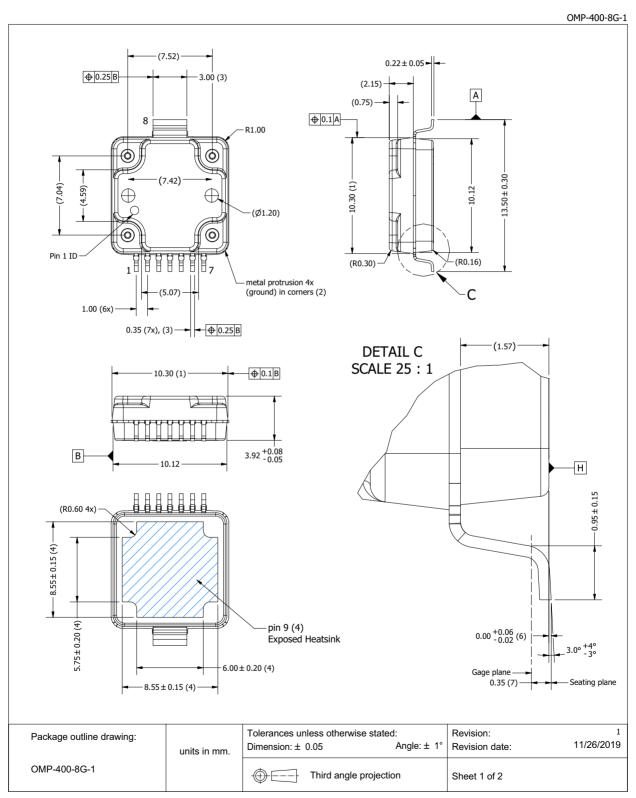


Fig 12. Package outline OMP-400-8G-1 (sheet 1 of 2)

OMP-400-8G-1

Drawing Notes				
Items	Description			
	Dimensions are excluding mold protrusion. Areas located adjacent to the leads have a maximum mold protrusion of 0.25			
(1)	mm (per side) and 0.62 mm max. in length. In between the 7 leads the protrusion is 0.25 mm max. At all other areas the			
	mold protrusion is maximum 0.15 mm per side. See also detail B.			
(2)	The metal protrusion (tie bars) in the corner will not stick out of the molding compound protrusions (detail A).			
(3)	The lead dambar (metal) protrusions are not included. Add 0.14 mm max to the total lead dimension at the dambar location			
(4)	The hatched area indicates the exposed heatsink. The dimensions represent the values between two opposite points along			
(4)	the original heatsink perimeter.			
(5)	The leads and exposed heatsink are plated with matte Tin (Sn).			
(0)	Dimension is measured with respect to the bottom of the heatsink Datum H. Positive value means that the bottom of the			
(6)	heatsink is higher than the bottom of the lead.			
(7)	Gage plane (foot length) to be measured from the seating plane.			

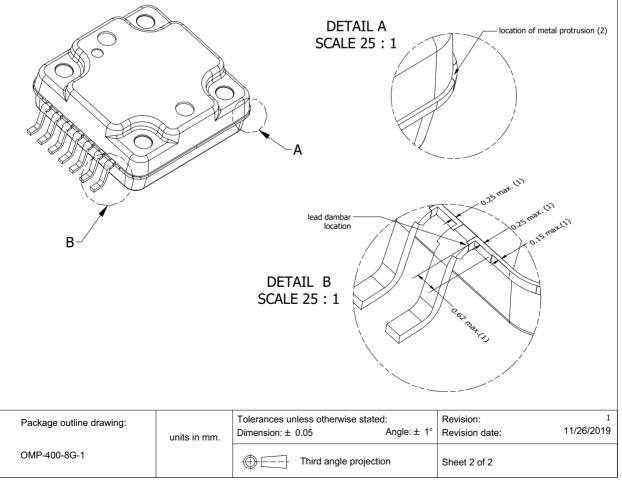


Fig 13. Package outline OMP-400-8G-1 (sheet 2 of 2)

10. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

Table 11. ESD sensitivity

ESD model	Class
Charged Device Model (CDM); According to ANSI/ESDA/JEDEC standard JS-002	C3 [1]
Human Body Model (HBM); According to ANSI/ESDA/JEDEC standard JS-001	1B 🛂

- [1] CDM classification C3 is granted to any part that passes after exposure to an ESD pulse of 1000 V.
- [2] HBM classification 1B is granted to any part that passes after exposure to an ESD pulse of 500 V.

11. Abbreviations

Table 12. Abbreviations

Acronym	Description
CCDF	Complementary Cumulative Distribution Function
CW	Continuous Wave
DPCH	Dedicated Physical CHannel
ESD	ElectroStatic Discharge
GEN10	Tenth Generation
GSM	Global System for Mobile Communications
LDMOS	Laterally Diffused Metal Oxide Semiconductor
LTE	Long Term Evolution
MMIC	Monolithic Microwave Integrated Circuit
MTF	Median Time to Failure
ОВО	Output Back Off
PAR	Peak-to-Average Ratio
RoHS	Restriction of Hazardous Substances
SMD	Surface Mounted Device
VSWR	Voltage Standing Wave Ratio
W-CDMA	Wideband Code Division Multiple Access

12. Revision history

Table 13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLM10D1822-61ABG v.1	20201019	Product data sheet	-	-

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.ampleon.com.

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LDMOS 2-stage integrated Doherty MMIC

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LDMOS 2-stage integrated Doherty MMIC

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